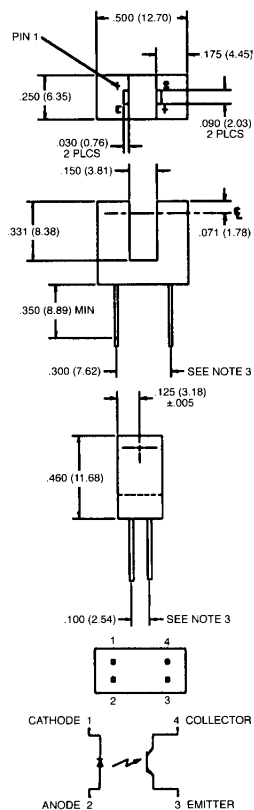


PACKAGE DIMENSIONS



ST2176

DESCRIPTION

The QVE11233 is designed to allow the user maximum flexibility in applications. Each switch consists of an infrared emitting diode facing an NPN phototransistor across a .150" (3.81 mm) gap.

FEATURES

- Lead spacing .300".
- Gap width of .150".
- Printed circuit board mounting.
- 2 mm aperture width.

NOTES:

1. DIMENSIONS ARE IN INCHES (mm).
2. TOLERANCE IS ±.010 (.25) UNLESS OTHERWISE SPECIFIED.
3. THIS DIMENSION IS CONTROLLED AT THE HOUSING SURFACE.

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Specified)

Storage Temperature	-40°C to $+85^\circ\text{C}$
Operating Temperature	-40°C to $+85^\circ\text{C}$
Soldering:	
Lead Temperature (Iron)	240°C for 5 sec. ^(2,3,4)
Lead Temperature (Flow)	260°C for 10 sec. ^(2,3)

INPUT DIODE

Continuous Forward Current	50 mA
Reverse Voltage	5.0 Volts
Power Dissipation	100 mW ⁽¹⁾

OUTPUT TRANSISTOR

Collector-Emitter Voltage	30.0 Volts
Emitter-Collector Voltage	5.0 Volts
Power Dissipation	100 mW ⁽¹⁾

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless Otherwise Specified)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
INPUT DIODE						
Forward voltage	V_F	—		1.70	V	$I_F = 20\text{ mA}$
Reverse Leakage Current	I_R	—		100	μA	$V_R = 2.0\text{ V}$
OUTPUT TRANSISTOR						
Emitter-Collector Breakdown	BV_{ECO}	5		—	V	$I_E = 100\text{ }\mu\text{A}$, $E_e = 0$
Collector-Emitter Breakdown	BV_{CEO}	30		—	V	$I_C = 1.0\text{ mA}$, $E_e = 0$
Collector-Emitter Leakage	I_{CEO}	—		100	nA	$V_{CE} = 10.0\text{ V}$, $E_e = 0$
COUPLED						
On-State Collector Current	$I_{C(ON)}$	0.50		—	mA	$I_F = 20\text{ mA}$, $V_{CE} = 5\text{ V}$
Saturation Voltage	$V_{CE(SAT)}$	—		0.40	V	$I_F = 20\text{ mA}$, $I_C = 0.25\text{ mA}$

NOTES

1. Derate power dissipation linearly $1.67\text{ mW}/^\circ\text{C}$ above 25°C .
2. RMA flux is recommended.
3. Methanol or Isopropyl alcohols are recommended as cleaning agents.
4. Soldering iron tip $1/16"$ (1.6 mm) from housing.



SLOTTED OPTICAL SWITCH

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.